

50V N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET IN SOT23

Features and Benefits

- $BV_{DSS} > 50V$
- $R_{DS(on)} \leq 3.5\Omega @ V_{GS} = 5V$
- Maximum continuous drain current $I_D = 200mA$
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

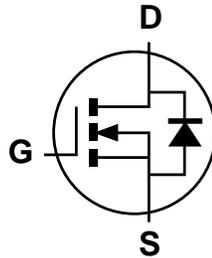
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matt Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

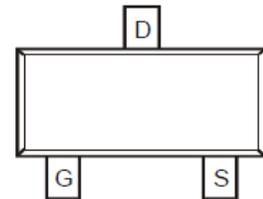
SOT-23



Top View



Device symbol



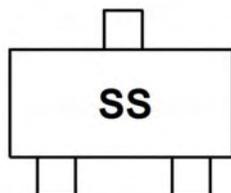
Pin-Out
Top View

Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BSS138TA	SS	7	8	3000

- Notes:
1. No purposefully added lead
 2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



SS = Product Type Marking Code

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

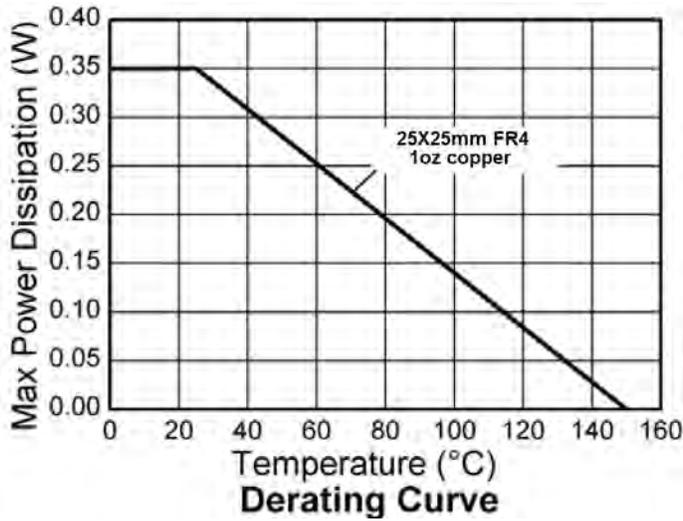
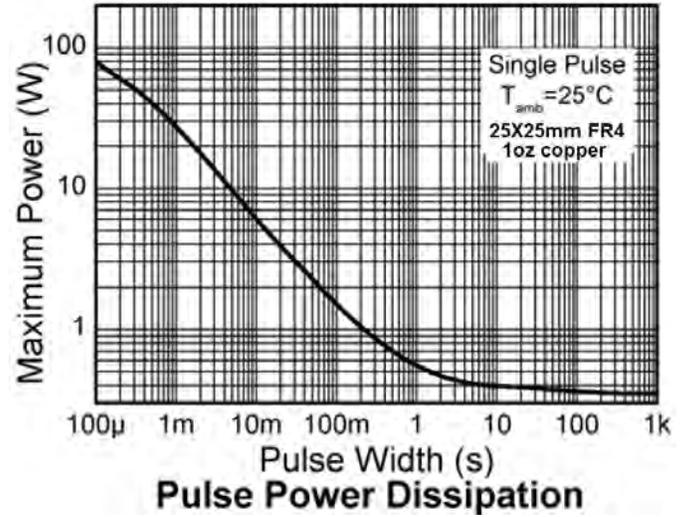
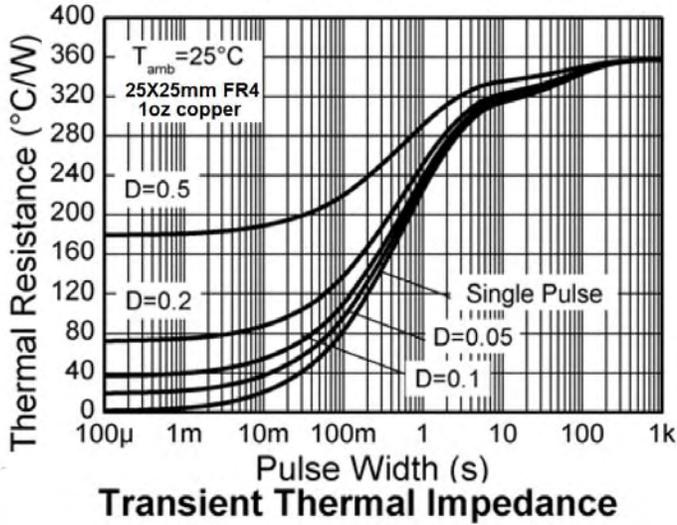
Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	200	mA
Pulsed Drain Current (Note 5)	I_{DM}	800	mA

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	350	mW
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Leads (Note 6)	$R_{\theta JL}$	195	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
4. For a device mounted on 25mm X 25mm X 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.
 5. Device mounted on minimum recommended pad layout test board, 10 μs pulse duty cycle = 1%.
 6. Thermal resistance from junction to solder-point (at the end of the collector lead).

Thermal Characteristics

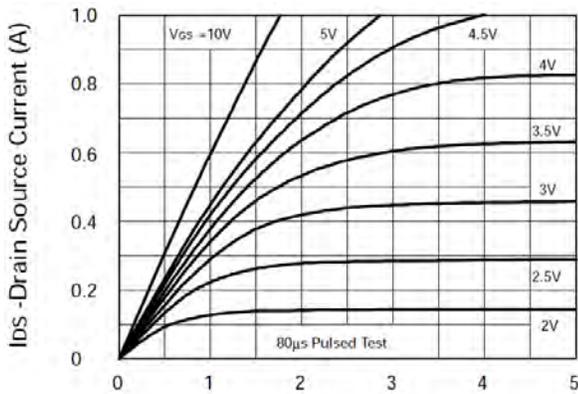


Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	50	-	-	V	$V_{GS} = 0V, I_D = 0.25mA$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	0.5 5 100	μA μA nA	$V_{DS} = 50V, V_{GS} = 0V$ $V_{DS} = 50V, V_{GS} = 0V, T_A = 125^\circ C$ $V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	-	1.5	V	$V_{DS} = V_{GS}, I_D = 1mA$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(on)}$	-	-	3.5	Ω	$V_{GS} = 5V, I_D = 200mA$
Forward Transconductance (Note 7 & 8)	g_{fs}	120	-	-	mS	$V_{DS} = 25V, I_D = 200mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	-	50	pF	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	-	25	pF	
Reverse Transfer Capacitance	C_{rss}	-	-	8	pF	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	-	10	-	ns	$V_{DD} = 30V, I_D = 280mA$
Turn-On Rise Time (Note 9)	t_r	-	10	-	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	-	15	-	ns	
Turn-Off Fall Time (Note 9)	t_f	-	25	-	ns	

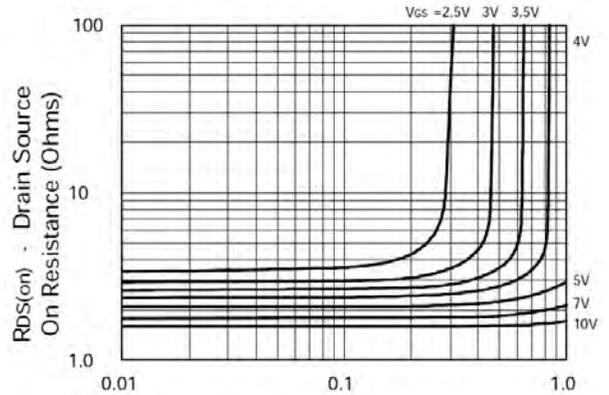
- Notes:**
- 7. Measured under pulsed conditions. Width = 300 μs . Duty cycle $\leq 2\%$.
 - 8. Sample test.
 - 9. Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator.

Electrical Characteristics



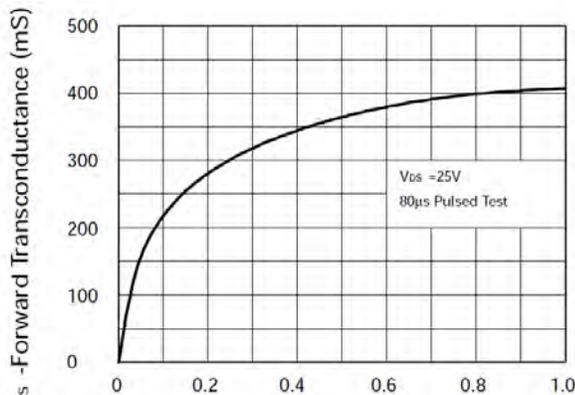
VDS -Drain Source Voltage (Volts)

Saturation Characteristics



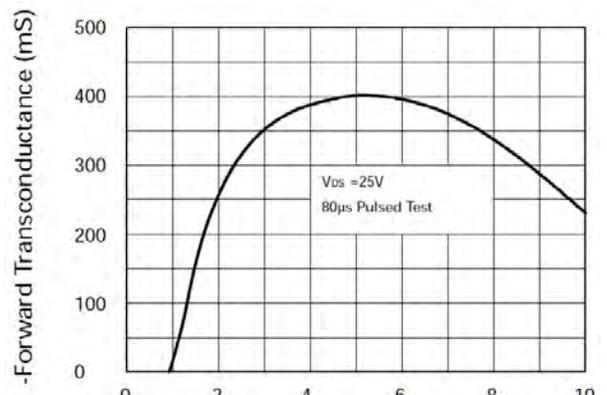
ID-Drain Current (Amperes)

Typical On Resistance vs. Drain Current



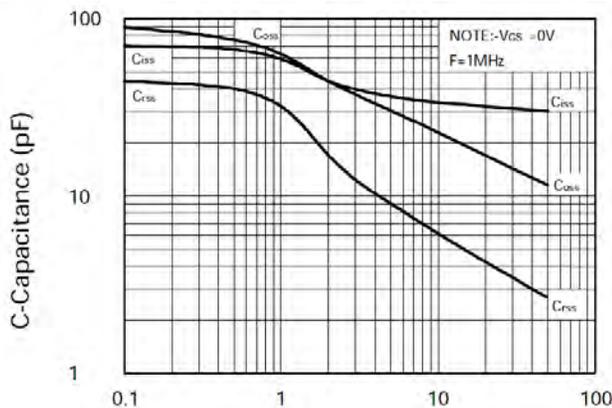
ID-Drain Current (Amperes)

Typical Transconductance vs. Drain Current



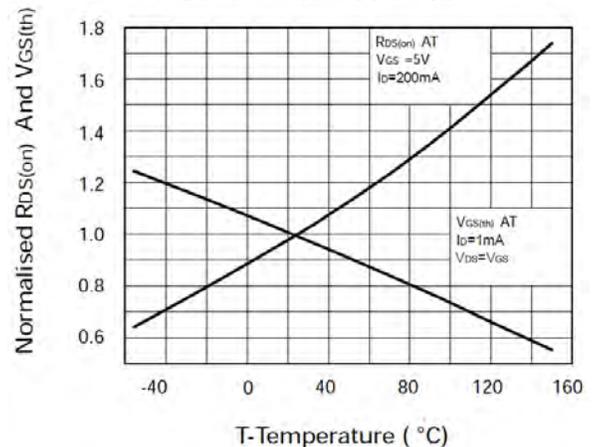
VGS -Gate Source Voltage (Volts)

Typical Transconductance vs. Gate - Source Voltage



VDS -Drain Source Voltage (Volts)

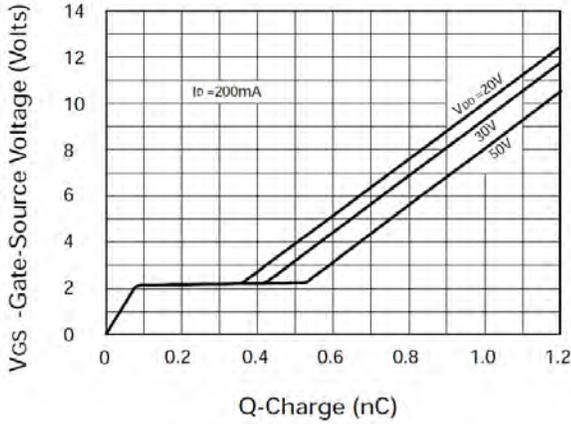
Typical Capacitance vs. Drain - Source Voltage



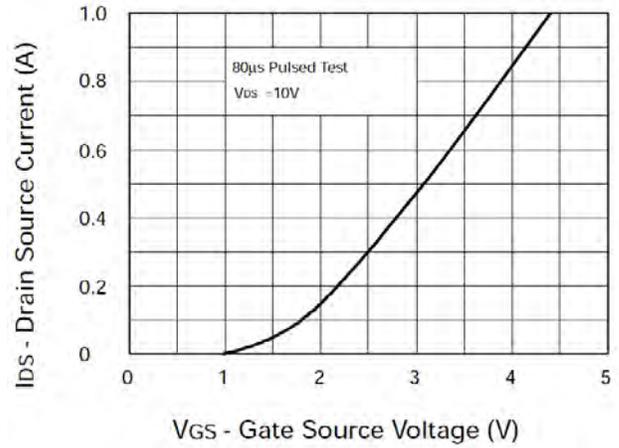
T-Temperature (°C)

Normalised RDS(on) And VGS(th) vs. Temperature

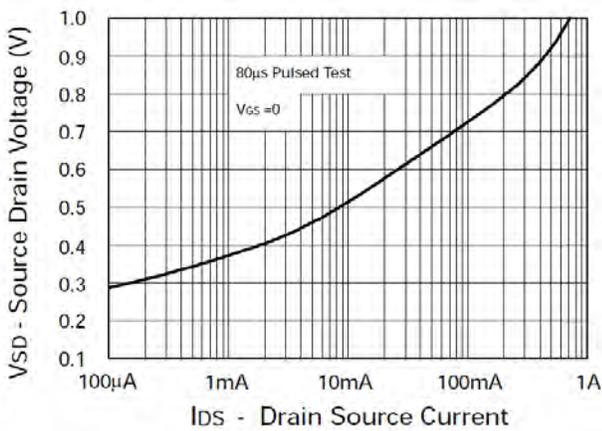
Electrical Characteristics – (Continuous)



Typical Gate Charge vs. Gate-Source Voltage

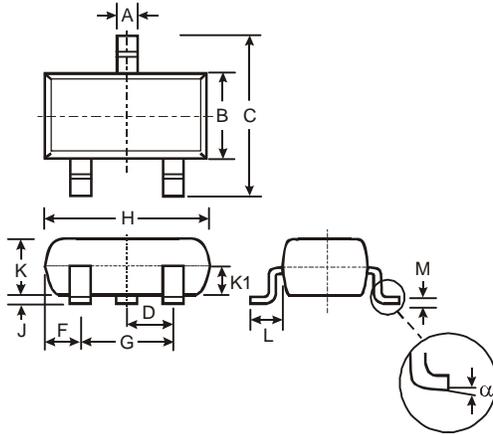


Typical Transfer Characteristics



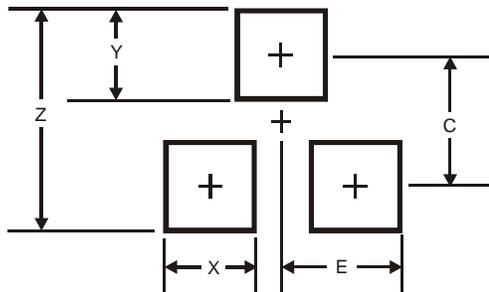
Typical Diode Forward Voltage

Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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